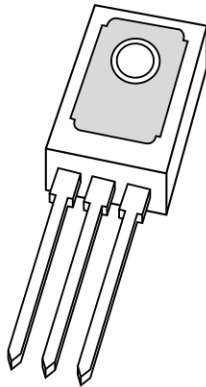


DATA SHEET



BD227; BD229; BD231 PNP power transistors

Product specification
Supersedes data of September 1994
File under Discrete Semiconductors, SC04

1997 Mar 04

PNP power transistors

BD227; BD229; BD231

FEATURES

- High current (max. 1.5 A)
- Low voltage (max. 80 V).

APPLICATIONS

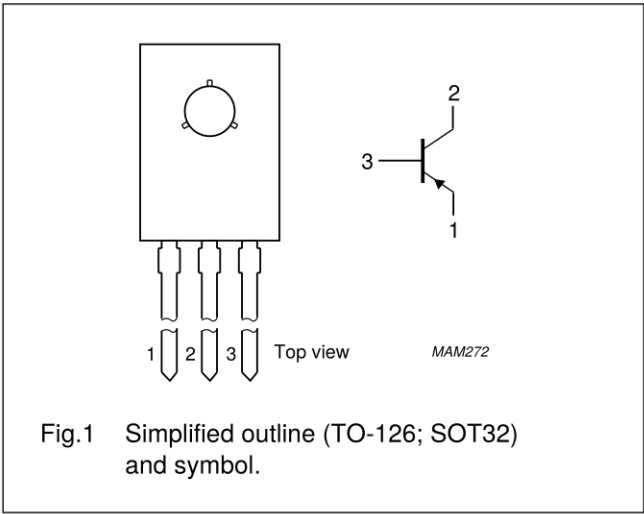
- Driver stages in television circuits.

DESCRIPTION

PNP power transistor in a TO-126; SOT32 plastic package. NPN complements: BD226, BD228 and BD230.

PINNING

PIN	DESCRIPTION
1	emitter
2	collector, connected to metal part of mounting surface
3	base



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	—	—	—	—
	BD227		—	—	—45	V
	BD229		—	—	—60	V
V_{CEO}	collector-emitter voltage	open base	—	—	—	—
	BD227		—	—	—45	V
	BD229		—	—	—60	V
I_{CM}	peak collector current		—	—	—3	A
			—	—	—	—
P_{tot}	total power dissipation	$T_{mb} \leq 62\text{ }^{\circ}\text{C}$	—	—	12.5	W
h_{FE}	DC current gain	$I_C = -150\text{ mA}; V_{CE} = -2\text{ V}$	40	—	250	—
		$I_C = -1\text{ A}; V_{CE} = -2\text{ V}$	25	—	—	—
f_T	transition frequency	$I_C = -50\text{ mA}; V_{CE} = -5\text{ V}; f = 100\text{ MHz}$	—	50	—	MHz

PNP power transistors

BD227; BD229; BD231

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter			
	BD227		—	−45	V
	BD229		—	−60	V
	BD231		—	−100	V
V_{CEO}	collector-emitter voltage	open base			
	BD227		—	−45	V
	BD229		—	−60	V
	BD231		—	−80	V
V_{EBO}	emitter-base voltage	open collector	—	−5	V
I_C	collector current (DC)		—	−1.5	A
I_{CM}	peak collector current		—	−3	A
I_{BM}	peak base current		—	−1	A
P_{tot}	total power dissipation	$T_{mb} \leq 62\text{ °C}$	—	12.5	W
T_{stg}	storage temperature		−65	+150	°C
T_j	junction temperature		—	150	°C
T_{amb}	operating ambient temperature		−65	+150	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	100	K/W
$R_{th\ j-mb}$	thermal resistance from junction to mounting base		7	K/W

Note

1. Refer to TO-126; SOT32 standard mounting conditions.

PNP power transistors

BD227; BD229; BD231

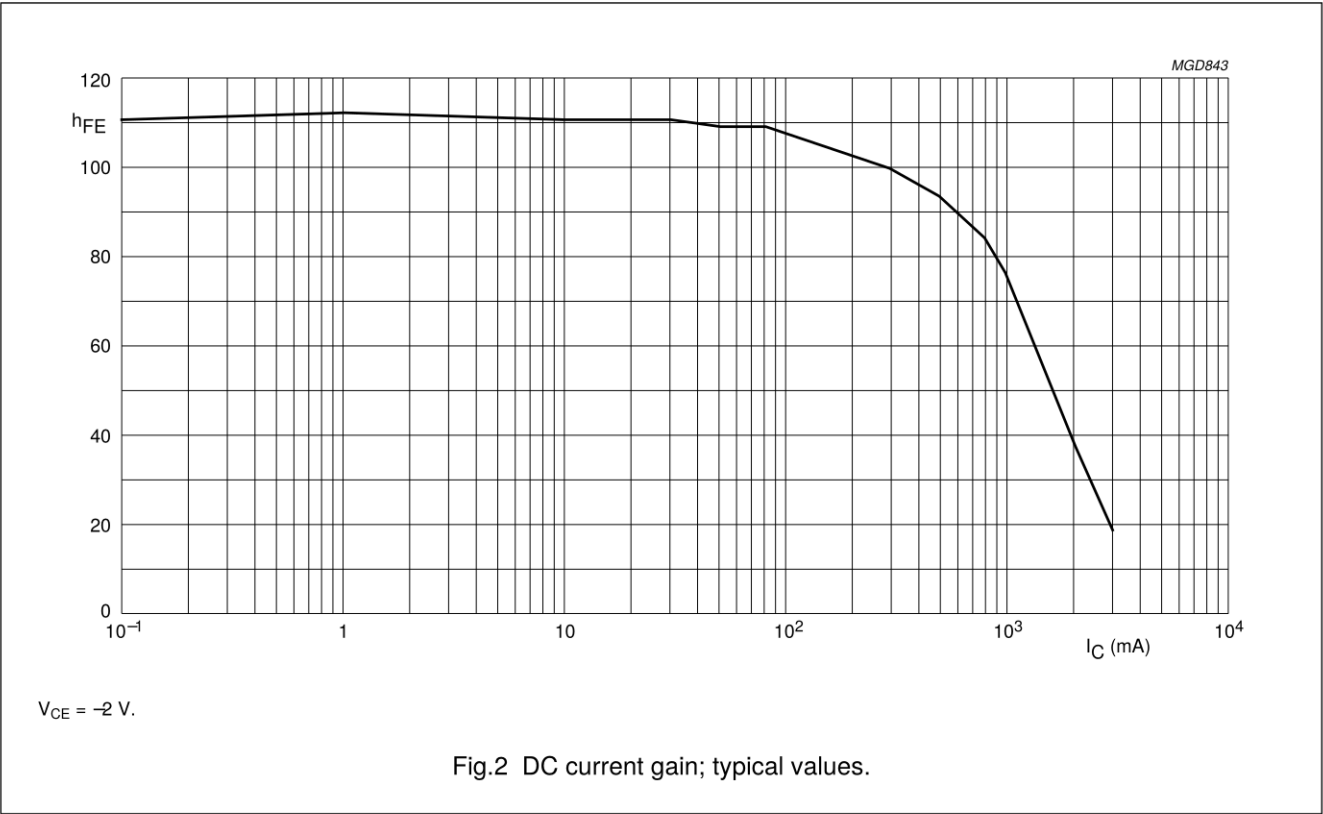
CHARACTERISTICS

T_j = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{CBO}	collector cut-off current	I _E = 0; V _{CB} = -30 V	—	—	-100	nA
		I _E = 0; V _{CB} = -30 V; T _j = 125 °C	—	—	-10	µA
I _{EBO}	emitter cut-off current	I _C = 0; V _{EB} = -5 V	—	—	-100	nA
h _{FE}	DC current gain	V _{CE} = -2 V; see Fig.2				
		I _C = -5 mA	40	—	—	
		I _C = -150 mA	40	—	250	
		I _C = -1 A	25	—	—	
V _{CEsat}	collector-emitter saturation voltage	I _C = -1 A; I _B = -0.1 A	—	—	-0.8	V
V _{BEsat}	base-emitter saturation voltage	I _C = -1 A; I _B = -0.1 A	—	—	-1.1	V
V _{BE}	base-emitter voltage	I _C = -1 A; V _{CE} = -2 V; note 1	—	—	-1.3	V
f _T	transition frequency	I _C = -50 mA; V _{CE} = -5 V; f = 100 MHz	—	50	—	MHz
$\frac{h_{FE1}}{h_{FE2}}$	DC current gain ratio of the complementary pairs	I _C = -150 mA; V _{CE} = -2 V	—	1.3	1.6	

Note

1. V_{BE} decreases by about -2.3 mV/K with increasing temperature.

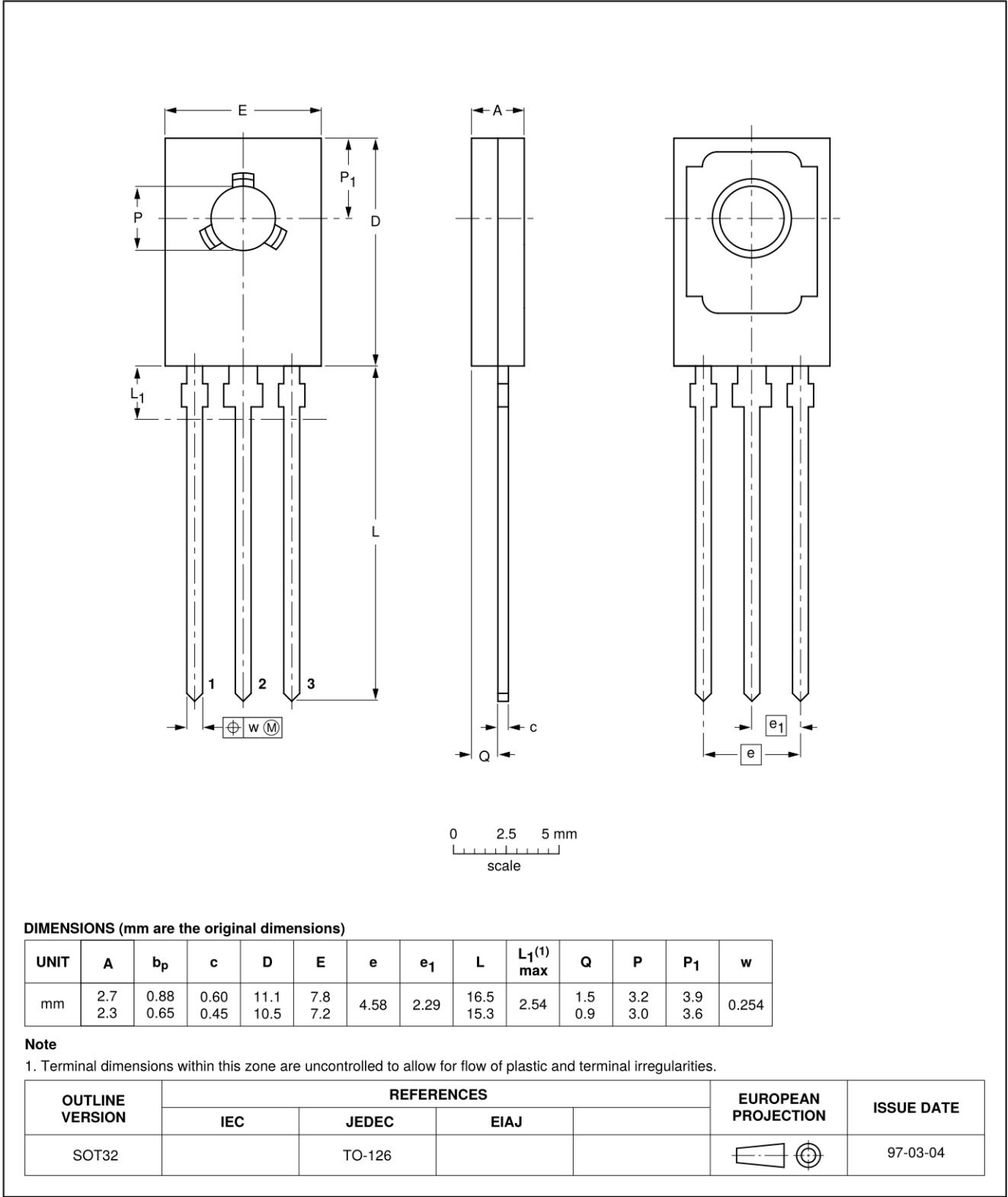


PNP power transistors

BD227; BD229; BD231

PACKAGE OUTLINE

Plastic single-ended leaded (through hole) package; mountable to heatsink, 1 mounting hole; 3 leads SOT32



PNP power transistors

BD227; BD229; BD231

DEFINITIONS

Data Sheet Status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

LIFE SUPPORT APPLICATIONS

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PNP power transistors

BD227; BD229; BD231

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